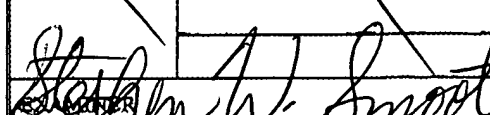


SEP 06 2005

SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION PTO-1449		ATTY. DOCKET NO. P102-US		SERIAL NO. 10/627,155							
		APPLICANT Patel, et al									
		FILING DATE 7/24/03		GROUP Not Yet Assigned 2813							
U.S. PATENT DOCUMENTS											
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE					
	2003/0160540	8/28/03	Miller, et al.								
	6,819,470	11/16/04	Meier, et al.								
	2003/0117688	6/26/03	Meier, et al.								
	2003/0117686	6/26/03	DiCarlo								
	2002/0093721	7/18/02	Kripe								
	6,724,510	4/20/04	Meyer, et al.								
	6,147,790	11/14/00	Meier, et al.								
	6,285,490	9/4/01	Meier, et al.								
	6,523,961	2/25/03	Ilkov, et al.								
	2002/0024641	2/28/02	Ilkov, et al.								
	2004/0004753	1/8/04	Pan								
FOREIGN PATENT DOCUMENTS											
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION					
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	WO 2004/001487	12/13/03	PCT			<input type="checkbox"/>	<input type="checkbox"/>				
	WO 2004/000720	12/13/03	PCT			<input type="checkbox"/>	<input type="checkbox"/>				
	WO 2004/001717	12/13/03	PCT			<input type="checkbox"/>	<input type="checkbox"/>				
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)											
											
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SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION PTO-1449		ATTY. DOCKET NO. P102-US		SERIAL NO. 10/627,155			
		APPLICANT Patel, et al					
		FILING DATE 7/24/03		GROUP Not Yet Assigned 2813			
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
	6,522,454	02/18/03	Meier, et al.				
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						<input type="checkbox"/>	<input type="checkbox"/>
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER	Stephen W. Smart			DATE CONSIDERED		1-9-2006	

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Substitute for form 1449A/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/627,155
		Filing Date	7/24/03
		First Named Inventor	Patel
		Art Unit	Not Yet Assigned 2813
		Examiner Name	Not Yet Assigned
Sheet 1 of 6	Attorney Docket Number	P102-US	

U.S. PATENT DOCUMENTS ¹					
Examiner Initials ²	Cite No. ³	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ⁴ (if known)			
		US- 6,511,737	05-12-1998	Haye, R.G.	
		US- 4,480,488	02-28-1980	Waters, H.P.	
		US- 4,319,989	12-12-1982	Plamm et al.	
		US- 4,488,968	02-12-1985	Cash et al.	
		US- 6,051,503	04-18-2000	Bhardwal, J.K.	
		US- 6,436,220	08-20-2002	Tal et al.	
		US- 6,482,387	12-18-2000	Tal et al.	
		US- 6,290,864 B1	09-18-2001	Patel et al.	
		US- 6,355,181 B1	03-12-2000	McQuarrie, A.D.	
		US- 2001/0002663 A1	08-07-2001	Tal et al.	
		US- 6,439,333	09-08-1998	Grant et al.	
		US- 2002/0033228 A1	03-21-2002	Leboulch et al.	
		US- 2002/0106534 A1	12-28-2002	Huthers, et al.	
		US- 2003/0064688 A1	03-20-2003	Patel et al.	
		US- 6,728,480	03-10-1998	Baker, K.S.	
		US- 2002/0185699	12-12-2002	Rold	
		US- 2002/0121682 A1	08-15-2002	Patel et al.	
		US- 5,836,258	11-18-1998	Huthers, A.	
		US- 2002/0047172 A1	04-29-2002	Rold	
		US- 2003/0186342 A1	09/04/03	Chen, et al.	

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Examiner Initials ²	Cite No. ³	Foreign Patent Document		Publication Date ⁴ MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁵
		Country Code ³	Number ⁴ and Code ⁴ (if known)				
		EP	0704884 A2	04-03-1996	Mohr, J.		
		EP	0822582 A1	02-04-1998	Bhardwal, J.K.		
		EP	0822584 A2	04-04-1998	Bhardwal, J.K.		
		WO	99/49588	09-30-1999	McQuarrie, A.D.		
		EP	0878824 A2	11-18-1998	McQuarrie et al.		
		EP	0878824 A3	01-19-2000	McQuarrie et al.		
		JP	1983/5788673 A	08-18-1983	Tsunetsugu, A.		
		JP	1983/56130328 A	08-04-1983	Yoshikawa et al.		
		JP	1986/50057938 A	04-09-1986	Katsumi et al.		
		WO	98/32143	07-23-1998	Tal et al.		

Examiner Signature	<i>Stephen H. Smart</i>	Date Considered	1-8-2006
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Substitute for form 1449A/PTO		Complete if Known:	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary).		Application Number	10/827.155
		Filing Date	7/24/03
		First Named Inventor	Patel
		Art Unit	Not Yet Assigned → 2813
		Examiner Name	Not Yet Assigned
Sheet 2 of 8	Attorney Docket Number	P102-US	

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No. 1	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code (if known)			
		US- 6,406,670-B1	05-28-2003	McGuire, et al.	
		US- 6,396,610-B1	05-28-2002	Hulbert, et al.	
		US- 6,578,483-B2	08/18/03	Lewin, et al.	
		US- 6,218,584	03-29-2001	Hawkins, et al.	
		US- 6,115,172	09-25-2000	Jeong	
		US- 6,204,080	09-20-2001	Hwang	
		US- 2003/0071015-A1	04/17/03	Chin, et al.	
		US- 2002/0464870-A1	11/07/02	Luong, et al.	
		US- 2002/0183851-A1	11/07/02	Gosel, et al.	
		US- 2002/0677876-A1	04/24/03	Kumar, et al.	
		US- 6,197,610-B4	02/03/2001	Toda	
		US- 6,580,360-B2	12/31/02	Sou, et al.	
		US- 2002/0424848-A1	07/03/02	Chen, et al.	
		US- 2003/0249086-A1	11/27/03	Rathner, et al.	
		US-			
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FOREIGN PATENT DOCUMENTS					
Examiner Initials	Cite No. 1	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code - Number - Kind Code (if known)			
		JP-1997108201581-A	09-23-1997	Kazuki, et al.	
		JP-1998/0343428-A	11-24-1998	Manabu, et al.	
		JP-1998/0347468-A	12-02-1998	McGuire, et al.	
		JP-1999/01187238-A	09-30-1999	Nobuo, et al.	
		JP-1999/01270830-A	12-01-1999	Toru, T.	
		JP-1997/02071247-A	04-01-1997	Toru, et al.	
		JP-1998/03466743-A	06-29-1998	Tedashi, F.	
		JP-1998/04062793-A	03-17-1998	Arata, et al.	
		JP-1998/01134019-A	06-24-1998	Shinji, et al.	
		JP-1998/01161121-A	06-12-1998	Shinji, et al.	

Examiner Signature	<i>Stephen W. Smart</i>	Date Considered	1-9-2006
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Substitute for form 1449B/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/827,155
		Filing Date	7/24/03
		First Named Inventor	Patel
		Group Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
		Attorney Docket Number	P102-US
Sheet	4	of	8

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS		
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issues number(s), publisher, city and/or country where published
		ALLEY et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching in F2 and XeF2 Gases: Ellipsometric Study", Surface Science 442 (1999), pp. 306-344.
		GLIDENHEISTER, J.M., "Xenon Diffusion Etching System" (Nov. 17, 1997).
		HASUKA et al., "Dominant Overall Chemical Reaction in a Chlorine Trifluoride-Silicon-Nitrogen System at Atmospheric Pressure", Japan Journal of Applied Physics Vol. 38 (1999), pp. 6460-6469.
		MESCHT et al., "A Novel X-ray Photoelectron Spectroscopy Study of the Al/SiO2 Interface", J. Appl. Phys. Vol. 67 (June 15, 1985), pp. 5258-5261.
		HOLLE, P.A., "Dynamics of SiF4 Desorption During Etching of Silicon by XeF2", IBM Almaden Research Center (Apr 16, 1987), pp. 186B-1872.
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		IBBOTSON et al., "Plasmaless Dry Etching of Silicon with Fluorine-containing Compounds", J. Appl. Phys. Vol. 56 No. 40 (Nov. 1984), pp. 2839-2842.
		IBBOTSON et al., "Comparison of XeF2 and F-atom Reactions with Si and SiO2", Applied Physics Letters, Vol. 44, 1425 (1984).
		STRELLER et al., "Selectivity in Dry Etching of Si (100) and XeF2 and VUV Light", Elsevier Science B.V., Applied Surface Science Vol. 106 (1996), pp. 241-246.
		VUGTS et al., "Si/XeF2 Etching: Temperature Dependence", J. Vac. Sci. Technol. A 14(5) (Sep/Oct 1996), pp. 2769-2774.
		WINTERS, H.F., "Etch Products from the Reaction of XeF2 with SiO2, SiO3, Si3N4, SiC, and Si in the Presence of Ion Bombardment", J. Vac. Sci. Technol. B 1(4) (Oct/Dec 1983), pp. 987-991.

Examiner Signature	<i>Stephen H. Smart</i>	Date Considered	1-9-2006
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Substitute for form 1449B/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/827,155
		Filing Date	7/24/03
		First Named Inventor	Patel
		Group Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
Sheet 5 of 8	Attorney Docket Number	P102-US	

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS		
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), (file of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		Kurt Williams, <i>Grit Rates for Micromachining Processing Part II</i> , 2003 IEEE, Pgs 784-778, Journal of Microelectromechanical Systems, Vol. 12, No. 8, December 2003.
		WINTERS et al., "The Etching of Silicon with XeF ₂ Vapor", Appl. Phys. Lett., Vol. 34(1) (January 1, 1979), pp. 70-72.
		XACTIX, Inc., Marketing Brochure (June 27, 1998).
		"Xenon Difluoride Isotropic Etch Systems: Seeing is Believing", Surface Technology Systems Ltd. brochure, Newport, UK (date unknown).
		CHU et al., "Controlled Pulse Etching with Xenon Difluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 10-19, 1997), pp. 689-688 (abstract only).
		SASSON et al., "Modeling and Optimizing XeF ₂ -enhanced P18 Milling of Silicon", 25th International Symposium for Testing and Failure Analysis, Santa Clara, CA (Nov. 4-18, 1999), pp. 235-281 (abstract only).
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		CHANG et al., "Gas Phase Silicon Micromachining with Silicon Difluoride", Proceedings of the SPIE - The International Society for Optical Engineering, Vol. 2641 (1995), pp. 117-128 (abstract only).

Examiner Signature	<i>Stephen W. Smart</i>	Date Considered	1-9-2006
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		Filing Date	7/24/03
		First Named Inventor	Patel
		Group Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
Sheet 6 of 6	Attorney Docket Number	P102-US	

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume/issue number(s), publisher, city and/or country where published	T ²
		SEBEL et al., "Reaction Layer Dynamics in Ion-Assisted Si/KaF ₂ Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 8, (Nov. 2000), pp. 2760-2769 (abstract only).	
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		SUGANO et al., "Study on KaF ₂ Photo Etching Using Wagon Wheel Pattern", Proceedings of the 1999-7 International Symposium on Micromechanics and Human Science: Towards the New Century, Nagoya, Japan (Nov. 23-25, 1999), pp. 163-187 (abstract only).	
		WARD et al., "Gas-Phase Silicon Etching with Bromine Trifluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 2 (June 16-19, 1997), pp. 4505-4508 (abstract only).	
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		TOGA et al., "Thin Beam Bulk Micromachining Based on RIE and Xenon Difluoride Silicon Etching", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16-19, 1997), pp. 671-674.	
		SEBEL et al., "Etching of Si Through a Thick Condensed KaF ₂ Layer", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 6 (Sept/Oct 2000), pp. 2080-2087 (abstract only).	

Examiner Signature	<i>Stephen H. Siroot</i>	Date Considered	1-9-2006
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